

BUK7Y07-30B

N-channel TrenchMOS standard level FET

Rev. 03 — 7 April 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V Loads
- Automotive systems
- General purpose power switch
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

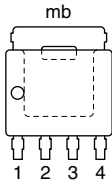
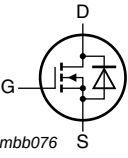
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 ; see Figure 4	[1]	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	105	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12 ; see Figure 13	-	5	7	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ Ω}$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	-	198	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 24\text{ V}$; $V_{GS} = 10\text{ V}$; see Figure 14	-	10.7	-	nC



[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		
			SOT669 (LFAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y07-30B	LFAK	plastic single-ended surface-mounted package (LFAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	30	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	-	30	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; [1] see Figure 4	-	-	75	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1	-	-	63	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; $t_p \leq 10\text{ }\mu\text{s}$; pulsed; see Figure 4	-	-	356	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	105	W
T_{stg}	storage temperature		-55	-	175	°C
T_j	junction temperature		-55	-	175	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$ [1]	-	-	75	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	-	356	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	-	198	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	see Figure 3 [2] [3] [4] [5]	-	-	-	J

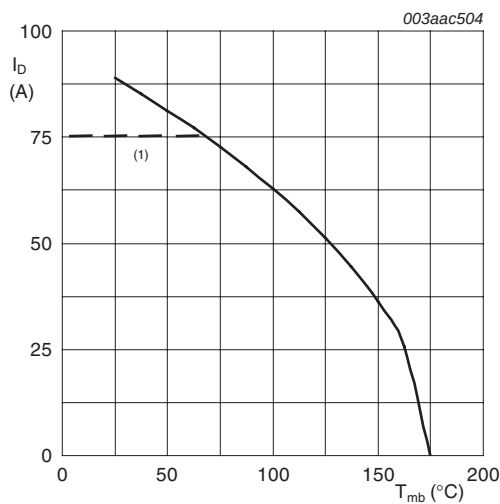
[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

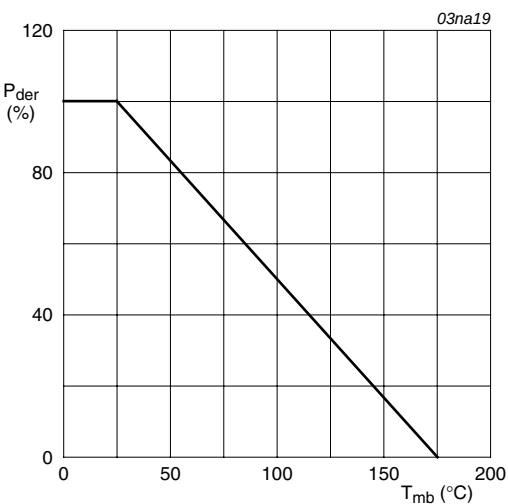
[4] Refer to application note AN10273 for further information.

[5] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.



$V_{GS} \geq 10\text{ V}$
(1) Capped at 75 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

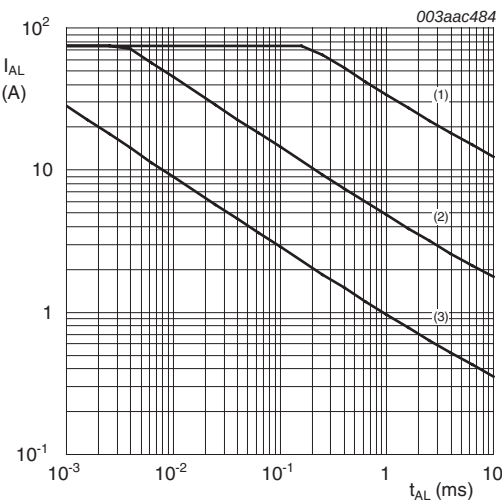
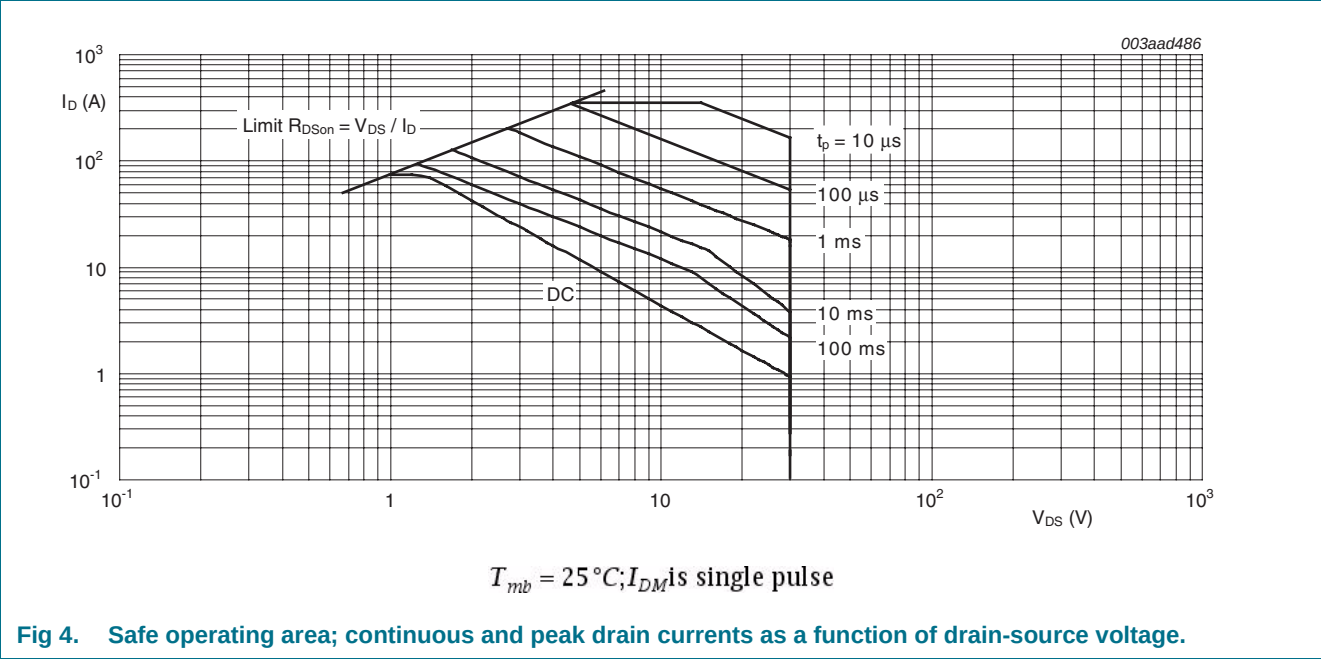


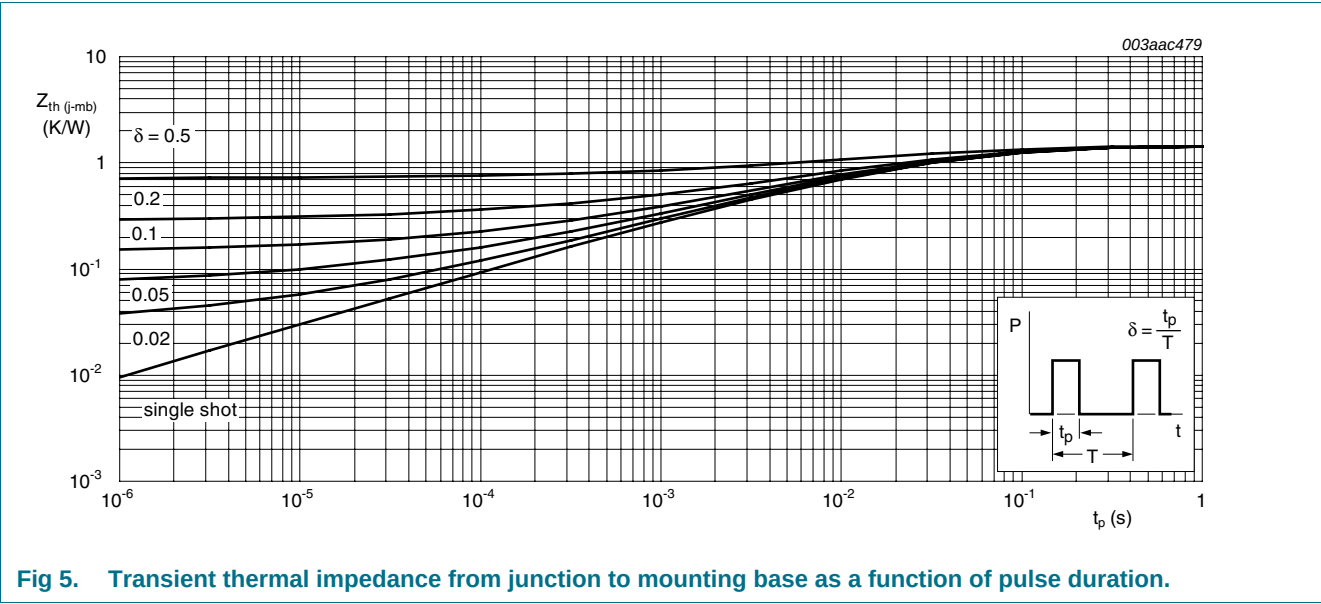
Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



5. Thermal characteristics

Table 5. Thermal characteristics

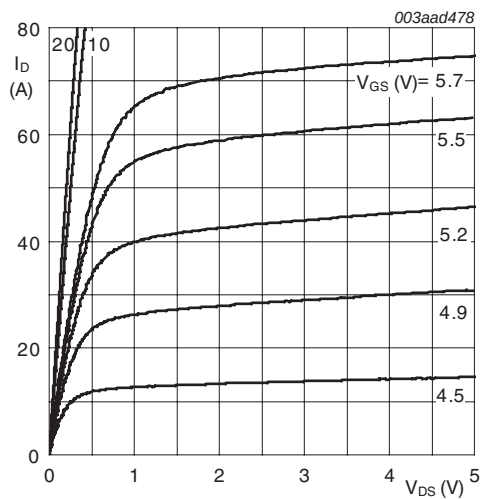
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1.42	K/W



6. Characteristics

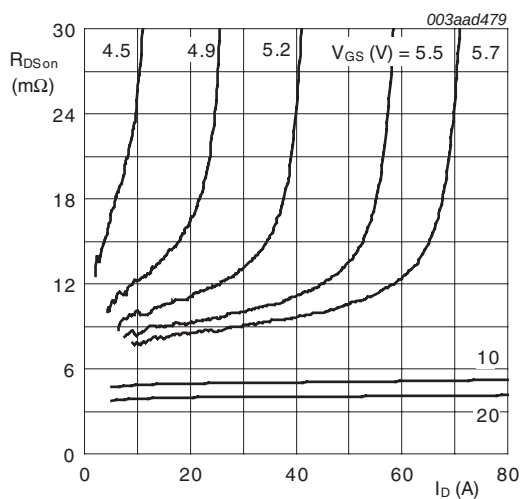
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _J = 25 °C	30	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _J = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25 °C; see Figure 10 ; see Figure 11	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = -55 °C; see Figure 10	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 175 °C; see Figure 10	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _J = 25 °C	-	0.02	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _J = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 20 V; T _J = 25 °C	-	2	100	nA
		V _{DS} = 0 V; V _{GS} = -20 V; T _J = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _J = 175 °C; see Figure 12 ; see Figure 13	-	-	13.4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _J = 25 °C; see Figure 12 ; see Figure 13	-	5	7	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 24 V; V _{GS} = 10 V; see Figure 14	-	31	-	nC
Q _{GS}	gate-source charge		-	9.5	-	nC
Q _{GD}	gate-drain charge		-	10.7	-	nC
C _{iss}	input capacitance		V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _J = 25 °C; see Figure 15	-	1330	1773
C _{oss}	output capacitance		-	495	594	pF
C _{rss}	reverse transfer capacitance		-	206	282	pF
t _{d(on)}	turn-on delay time	V _{DS} = 25 V; R _L = 1 Ω; V _{GS} = 10 V; R _{G(ext)} = 10 Ω	-	17	-	ns
t _r	rise time		-	30	-	ns
t _{d(off)}	turn-off delay time		-	40	-	ns
t _f	fall time		-	28	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _J = 25 °C; see Figure 16	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 25 V	-	39	-	ns
Q _r	recovered charge		-	53	-	nC



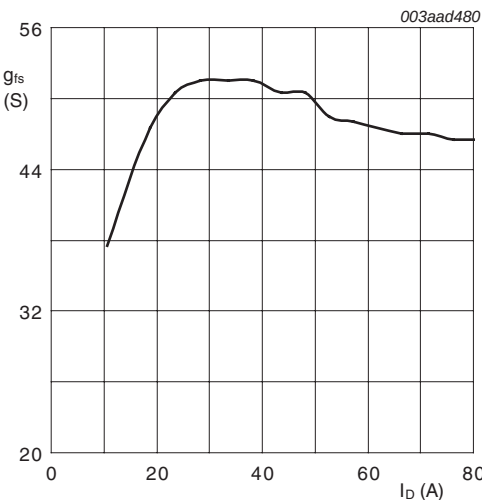
$T_j = 25\text{ }^{\circ}\text{C}$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.



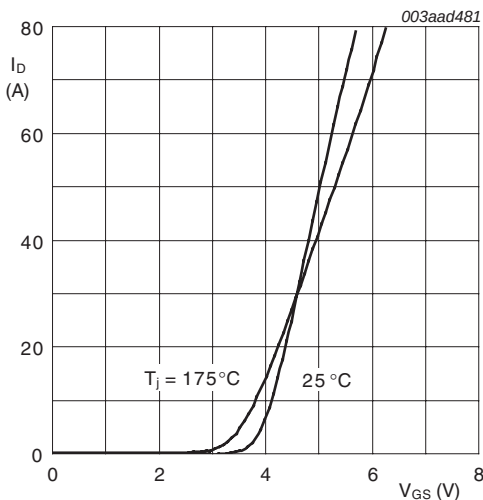
$T_j = 25\text{ }^{\circ}\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 25\text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values.



$V_{DS} = 25\text{ V}$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

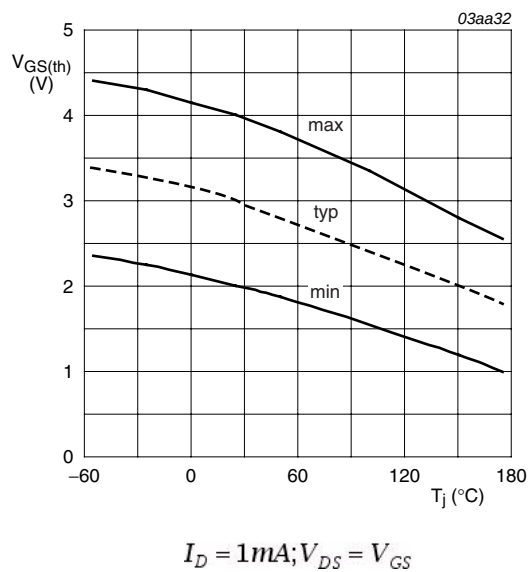


Fig 10. Gate-source threshold voltage as a function of junction temperature

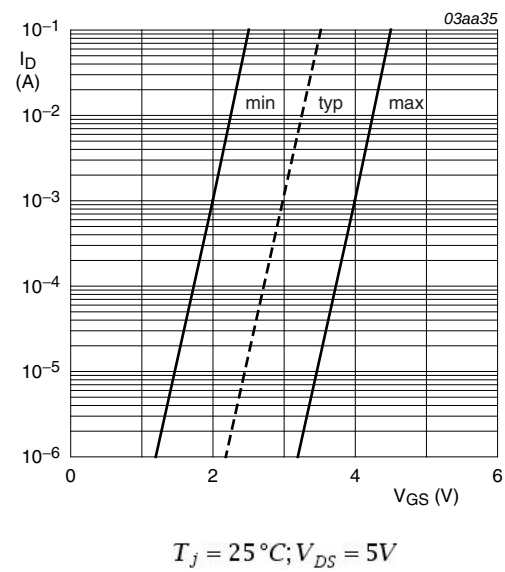


Fig 11. Sub-threshold drain current as a function of gate-source voltage

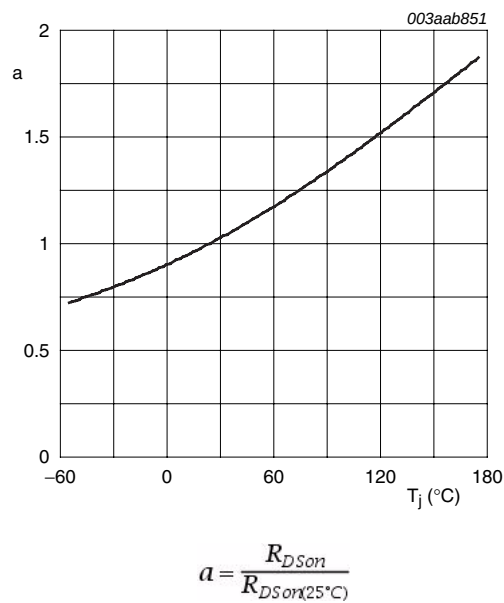


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

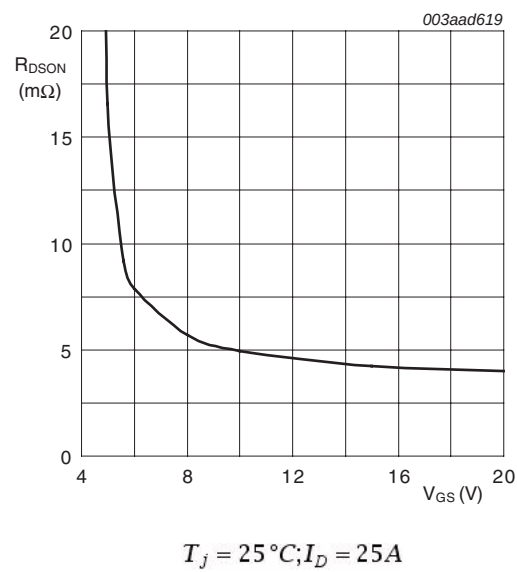
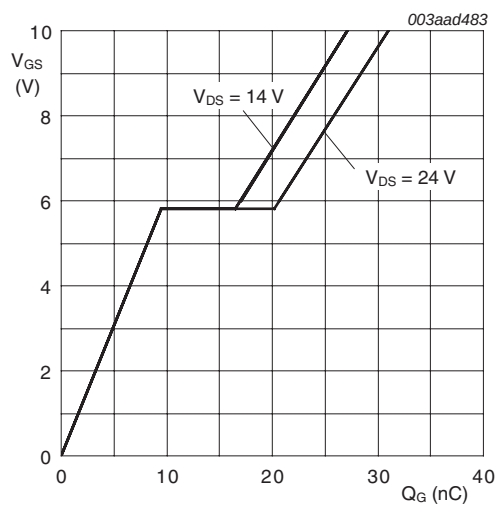
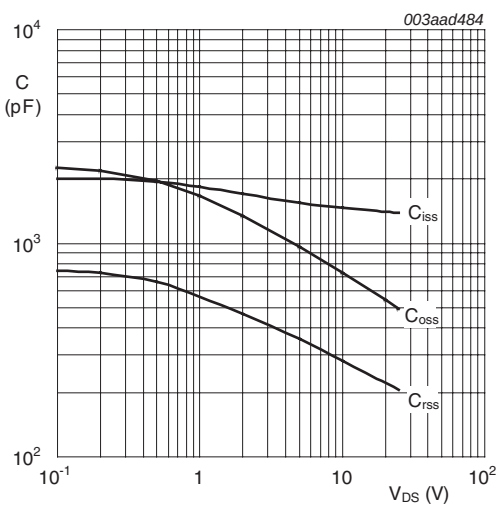


Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.



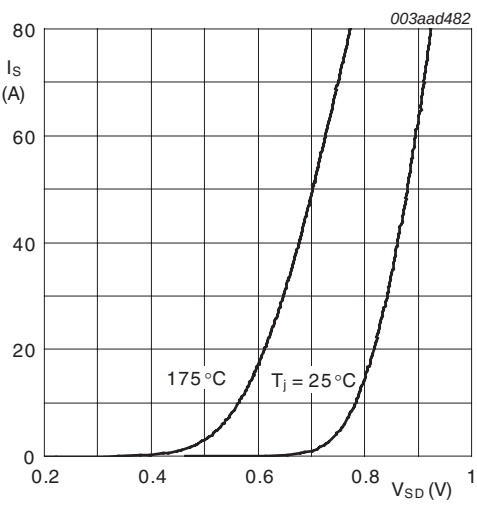
$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values.



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$V_{GS} = 0\text{ V}$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

7. Package outline

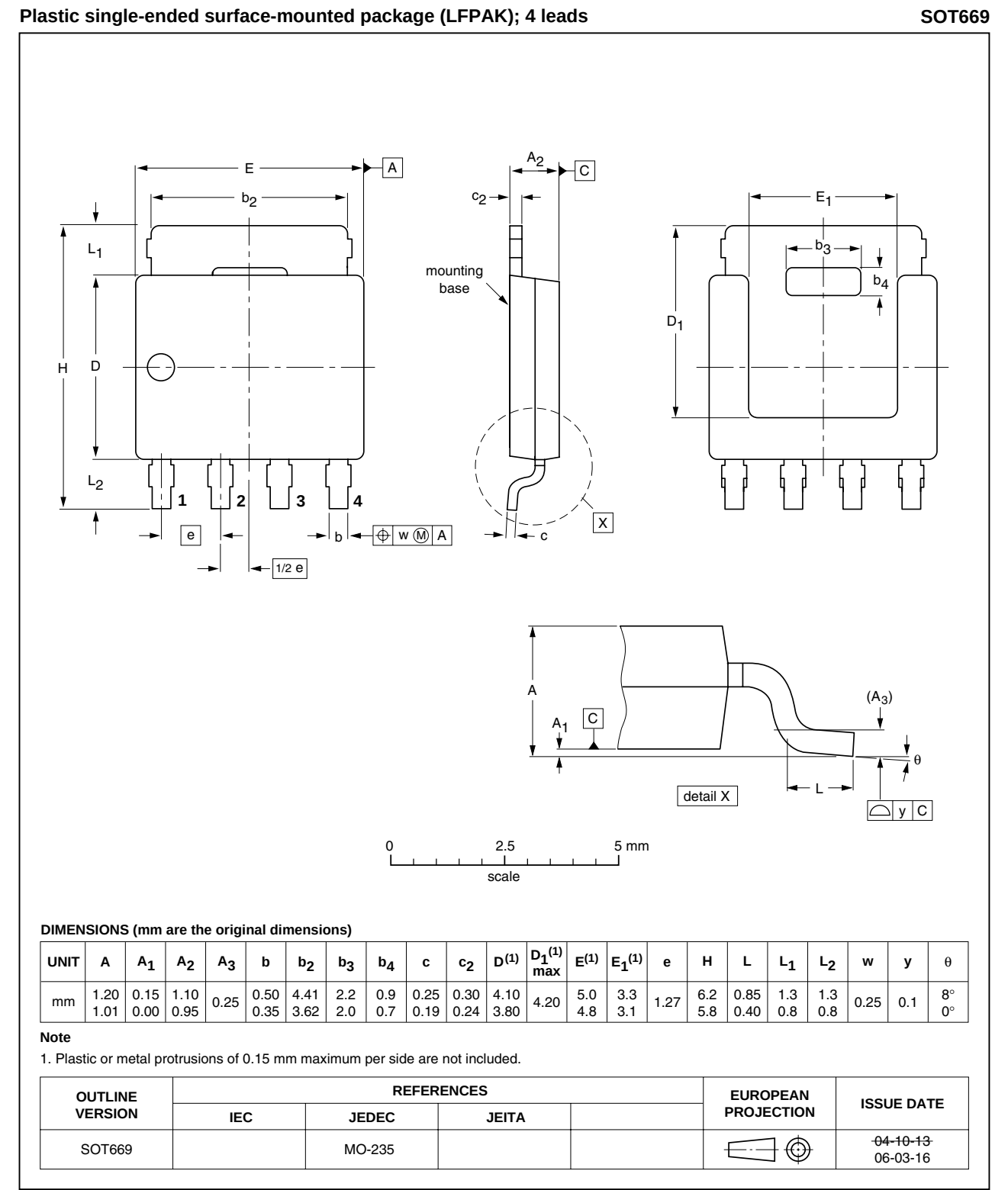


Fig 17. Package outline SOT669 (LPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y07-30B_3	20100407	Product data sheet	-	BUK7Y07-30B_2
Modifications:		• Status changed from objective to product.		
BUK7Y07-30B_2	20100215	Objective data sheet	-	BUK7Y07-30B_1

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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